

Ultrafast Rectifier

INCHANGE SEMICONDUCTOR

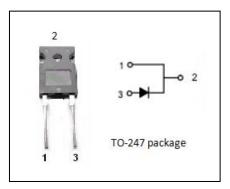
FDRW35S60L

FEATURES

- Guarding for over voltage protection
- Low forward voltage, high efficiency
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

 These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
VRRM	Peak Repetitive Reverse Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current	35	А
IFSM	Non-repetitive Peak Surge Current	140	А
TJ	Max.Junction Temperature	150	°C
Tstg	Storage Temperature Range	-40~150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C) (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤2%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
VF	Maximum Instantaneous Forward Voltage	I _F = 35A	2.6	v
IR	Maximum Instantaneous Reverse Current	VR=V _{RRM}	250	μA
trr	Maximum Reverse Recovery Time	IF =1A	36	ns

NOTICE:

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